

IN THE CLAIMS

Please delete claims 16-24 below.

1. (Original) A semiconductor device comprising:

a sealing member formed of an insulating resin and having an upper surface and a lower surface as a surface and a back surface, respectively, and side faces connecting the upper and lower surfaces with each other;

a semiconductor chip positioned within the sealing member, the semiconductor chip including electrodes respectively on a first main surface and a second main surface thereof as a surface and a back surface, respectively;

a first electrode plate having an upper surface and a lower surface as a surface and a back surface, respectively, a part of the upper surface of the first electrode plate being exposed to the upper surface of the sealing member and the lower surface portions of end portions of the first electrode plate being exposed to the lower surface of the sealing member; and

a second electrode plate having an upper surface and a lower surface as a surface and a back surface, respectively, the lower surface of the second electrode plate being exposed to the lower surface of the sealing member and the upper surface of the second electrode plate being positioned within the sealing member,

wherein the electrode on the second main surface of the semiconductor chip is electrically connected to the first or the second electrode plate through an electrically conductive adhesive, and

wherein a bump electrode is formed on a surface of the electrode formed on the first main surface of the semiconductor chip, the bump electrode is covered with an electrically conductive adhesive, and the bump electrode and the second or the first electrode plate are electrically connected to each other through the adhesive.

2. (Original) A semiconductor device according to claim 1, wherein the bump electrode and the second or the first electrode plate are not in contact with each other.

3. (Original) A semiconductor device according to claim 1, wherein the bump electrode is provided one or plurally on the electrode surface.

4. (Original) A semiconductor device according to claim 1, wherein the bump electrode is a stud type bump electrode formed on the electrode provided on the first main surface of the semiconductor chip.
5. (Original) A semiconductor device according to claim 1, wherein the bump electrode is a stud type bump electrode formed on the electrode provided on the first main surface of the semiconductor chip, and the bump electrode is provided plurally on the electrode surface, of which the bump electrode(s) having a large height is (are) in contact with the first or the second electrode plate and the other bump electrode(s) is (are) not in contact with the first or the second electrode plate.
6. (Original) A semiconductor device according to claim 1, wherein a recess is formed in the surface of the first or the second electrode plate in an opposed relation to the bump electrode.
7. (Original) A semiconductor device according to claim 1, wherein ends of the electrode plates project to the outside from the side faces of the sealing member.
8. (Original) A semiconductor device according to claim 1, wherein ends of the electrode plates are each branched to plural branch ends which project to the outside from the side faces of the sealing member.
9. (Original) A semiconductor device according to claim 1, wherein the first electrode plate and the second electrode plate extend in different directions.
10. (Original) A semiconductor device according to claim 1, wherein the electrode provided on the semiconductor chip on which the bump electrode is formed is formed by an aluminum film.
11. (Original) A semiconductor device according to claim 1, wherein the bump electrode is formed by gold wire or copper wire, and the adhesive is comprised of silver paste having been cured.

12. (Original) A semiconductor device according to claim 1, wherein the spacing between the first main surface of the semiconductor chip and the electrode plates which confront the first main surface of the chip is about 10 to 30 μm .
13. (Original) A semiconductor device according to claim 1,
wherein a transistor is formed on the semiconductor chip, and a second electrode of the transistor is formed on the second main surface of the semiconductor chip,
wherein a first electrode and a control electrode of the transistor are formed on the first main surface of the semiconductor chip,
wherein the first or the second electrode plate is provided plurally, the second electrode is connected to the second or the first electrode plate, and
wherein the first electrode and the control electrode are connected separately to the plural first or second electrode plates.
14. (Original) A semiconductor device according to claim 1, wherein the adhesive which covers the bump electrode is spread over both the electrode region in which the bump electrode is formed and a region deviated from the electrode region and reaching positions near ends of the semiconductor chip.
15. (Original) A semiconductor device according to claim 1,
wherein the sealing member is in a quadrangular shape having four of said side faces,
wherein ends of the first electrode plate project from a pair of opposed side faces of the sealing member, and
wherein ends of the second electrode plate project from the other pair of side faces intersecting said pair of opposed side faces of the sealing member.

16-24 (Canceled)